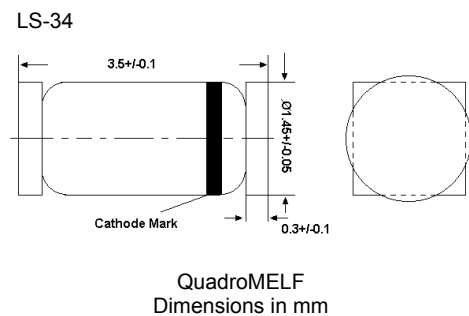


BZT2V0...BZT200

Silicon Epitaxial Planar Zener Diodes

In QuadroMELF case especially for automatic insertion. The Zener voltages are graded according to the international E24 standard. Other tolerance, Non-standard and higher Zener voltages upon request.



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^\circ\text{C}$
¹⁾ Valid provided that electrodes are kept at ambient temperature			

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R_{thA}	0.3 ¹⁾	K/mW
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1	V
¹⁾ Valid provided that electrodes are kept at ambient temperature			



BZT2V0...BZT200

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Type	Zener Voltage ¹⁾			Dynamic Resistance			Reverse Leakage Current			Temp coefficient of Zener Voltage
	V_{Znom}	V_{ZT}	at I_{ZT}	Z_{ZT}	Z_{ZK}	at I_{ZK}	$T_a = 25\text{ }^{\circ}\text{C}$	$T_a = 125\text{ }^{\circ}\text{C}$	at V_R	
	(V)	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (μA)	Max. (μA)	(V)	
BZT2V0	2	1.8...2.15	5	85	600	1	100	200	1	-0.09...-0.06
BZT2V2	2.2	2.08...2.33	5	85	600	1	75	160	1	-0.09...-0.06
BZT2V4	2.4	2.28...2.56	5	85	600	1	50	100	1	-0.09...-0.06
BZT2V7	2.7	2.5...2.9	5	85	600	1	10	50	1	-0.09...-0.06
BZT3V0	3	2.8...3.2	5	85	600	1	4	40	1	-0.08...-0.05
BZT3V3	3.3	3.1...3.5	5	85	600	1	2	40	1	-0.08...-0.05
BZT3V6	3.6	3.4...3.8	5	85	600	1	2	40	1	-0.08...-0.05
BZT3V9	3.9	3.7...4.1	5	85	600	1	2	40	1	-0.08...-0.05
BZT4V3	4.3	4...4.6	5	75	600	1	1	20	1	-0.06...-0.03
BZT4V7	4.7	4.4...5	5	60	600	1	0.5	10	1	-0.05...+0.02
BZT5V1	5.1	4.8...5.4	5	35	550	1	0.1	2	1	-0.02...+0.02
BZT5V6	5.6	5.2...6	5	25	450	1	0.1	2	1	-0.05...+0.05
BZT6V2	6.2	5.8...6.6	5	10	200	1	0.1	2	2	0.03...0.06
BZT6V8	6.8	6.4...7.2	5	8	150	1	0.1	2	3	0.03...0.07
BZT7V5	7.5	7...7.9	5	7	50	1	0.1	2	5	0.03...0.07
BZT8V2	8.2	7.7...8.7	5	7	50	1	0.1	2	6.2	0.03...0.08
BZT9V1	9.1	8.5...9.6	5	10	50	1	0.1	2	6.8	0.03...0.09
BZT10	10	9.4...10.6	5	15	70	1	0.1	2	7.5	0.03...0.10
BZT11	11	10.4...11.6	5	20	70	1	0.1	2	8.2	0.03...0.11
BZT12	12	11.4...12.7	5	20	90	1	0.1	2	9.1	0.03...0.11
BZT13	13	12.4...14.1	5	26	110	1	0.1	2	10	0.03...0.11
BZT15	15	13.8...15.6	5	30	110	1	0.1	2	11	0.03...0.11
BZT16	16	15.3...17.1	5	40	170	1	0.1	2	12	0.03...0.11
BZT18	18	16.8...19.1	5	50	170	1	0.1	2	13	0.03...0.11
BZT20	20	18.8...21.2	5	55	220	1	0.1	2	15	0.04...0.11
BZT22	22	20.8...23.3	5	55	220	1	0.1	2	16	0.04...0.12
BZT24	24	22.8...25.6	5	80	220	1	0.1	2	18	0.04...0.12
BZT27	27	25.1...28.9	5	80	220	1	0.1	2	20	0.04...0.12
BZT30	30	28...32	5	80	220	1	0.1	2	22	0.04...0.12
BZT33	33	31...35	5	80	220	1	0.1	2	24	0.04...0.12
BZT36	36	34...38	5	80	220	1	0.1	2	27	0.04...0.12
BZT39	39	37...41	5	90	500	0.5	0.1	5	30	0.04...0.12
BZT43	43	40...46	2.5	90	500	0.5	0.1	5	33	0.04...0.12
BZT47	47	44...50	2.5	110	600	0.5	0.1	5	38	0.04...0.12
BZT51	51	48...54	2.5	125	700	0.5	0.1	10	39	0.04...0.12
BZT56	56	52...60	2.5	135	700	0.5	0.1	10	43	0.04...0.12
BZT62	62	58...66	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
BZT68	68	64...72	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
BZT75	75	70...79	2.5	250	1000	0.5	0.1	10	56	0.04...0.12
BZT82	82	77...87	2.5	300	1500	0.25	0.1	10	62	0.05...0.12
BZT91	91	85...96	2.5	450	2000	0.1	0.1	10	68	0.05...0.12
BZT100	100	94...106	1	450	5000	0.1	0.1	10	75	0.05...0.12
BZT110	110	104...116	1	600	5000	0.1	0.1	10	82	0.05...0.12
BZT120	120	114...127	1	800	5500	0.1	0.1	10	91	0.05...0.12
BZT130	130	124...141	1	950	6000	0.1	0.1	10	100	0.05...0.12
BZT150	150	138...156	1	1250	6500	0.1	0.1	10	110	0.05...0.12
BZT160	160	153...171	1	1400	7000	0.1	0.1	10	120	0.05...0.12
BZT180	180	168...191	1	1700	8500	0.1	0.1	10	130	0.05...0.12
BZT200	200	188...212	1	2000	10000	0.1	0.1	10	150	0.05...0.12

¹⁾ Tested with pulses $t_p = 20\text{ ms}$.



CHANGZHOU GUANGDA ELECTRONIC CO. LTD

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